

GT8G134

Strobe Flash Applications

- Compact and Thin (TSSOP-8) package
- Enhancement-mode
- Peak collector current: $I_C = 150\text{ A (max)}$
(@ $V_{GE}=2.5\text{V(min)}$)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	400	V
Gate-emitter voltage	DC	V_{GES}	± 4
	Pulse	V_{GES}	± 5
Collector current	Pulse (Note 1)	I_{CP}	150 A
Collector power dissipation (t=10 s)	(Note 2a)	$P_C (1)$	1.1 W
	(Note 2b)	$P_C (2)$	0.6 W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

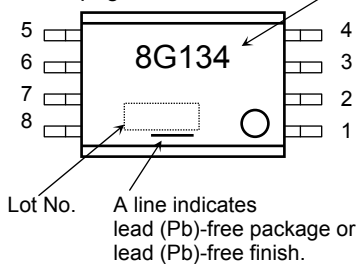
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

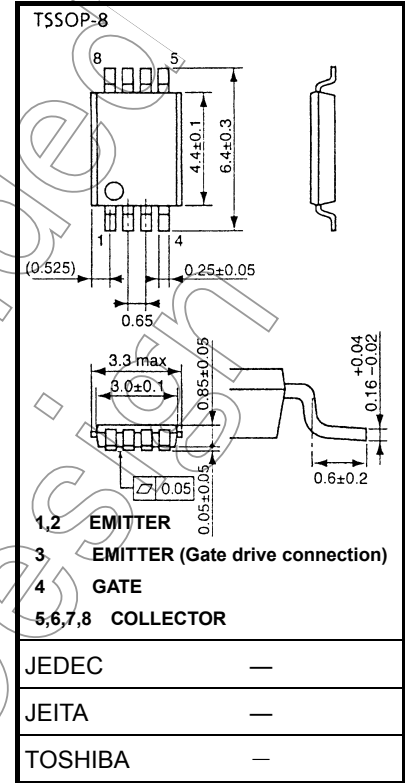
Characteristics	Symbol	Rating	Unit
Thermal resistance, junction to ambient (t = 10 s) (Note2a)	$R_{th(j-a)} (1)$	114	°C/W
Thermal resistance, junction to ambient (t = 10 s) (Note2b)	$R_{th(j-a)} (2)$	208	°C/W

Marking (Note 3)

Note : For (Note 1) , (Note 2a) , (Note 2b) and (Note 3) , Please refer to the next page.

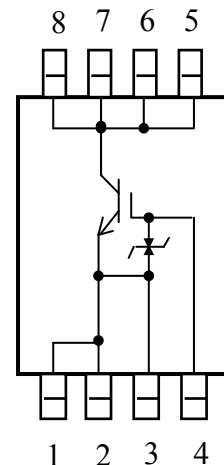


Unit: mm



Weight: 0.035 g (typ.)

Circuit Configuration



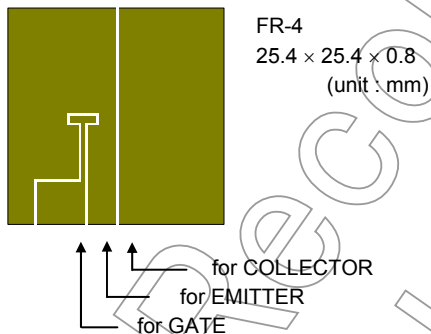
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GES}	$V_{GE} = \pm 4 \text{ V}, V_{CE} = 0$	—	—	± 10	μA
Collector cut-off current		I_{CES}	$V_{CE} = 400 \text{ V}, V_{GE} = 0$	—	—	10	μA
Gate-emitter cut-off voltage		$V_{GE}(\text{OFF})$	$I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}$	0.65	1.0	1.35	V
Collector-emitter saturation voltage		$V_{CE}(\text{sat})$	$I_C = 150 \text{ A}, V_{GE} = 2.5 \text{ V}$	—	3.4	—	V
Input capacitance		C_{ies}	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	—	4560	—	pF
Switching time	Rise time	t_r		—	0.6	—	μs
	Turn-on time	t_{on}		—	0.8	—	
	Fall time	t_f		—	1.2	—	
	Turn-off time	t_{off}		—	1.8	—	

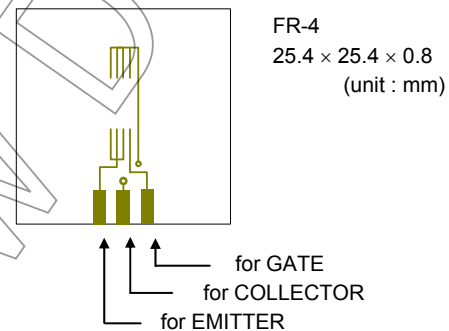
Note

Note 1: Please use devices on condition that the junction temperature is below 150°C.
 Repetitive rating: pulse width limited by maximum junction temperature.

Note 2a : Device mounted on a glass-epoxy board (a)

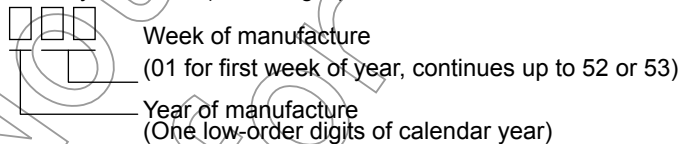


Note 2b : Device mounted on a glass-epoxy board (b)



Note 3: ○ on lower right of the marking indicates Pin 1.

※ Weekly code: (Three digits)



※ Pb-Free Finish (Only a coating lead terminal) :

It is marking about an underline to a week of manufacture mark.



Caution on handling

This device is MOS gate type. Therefore , please care of a protection from ESD in your handling .

Caution in design

You should be design dv/dt value under Icp=150A is below 400 V/μs when IGBT turn off under Ta=70°C .
 You should be design to don't flow collector current through terminal number 3 .

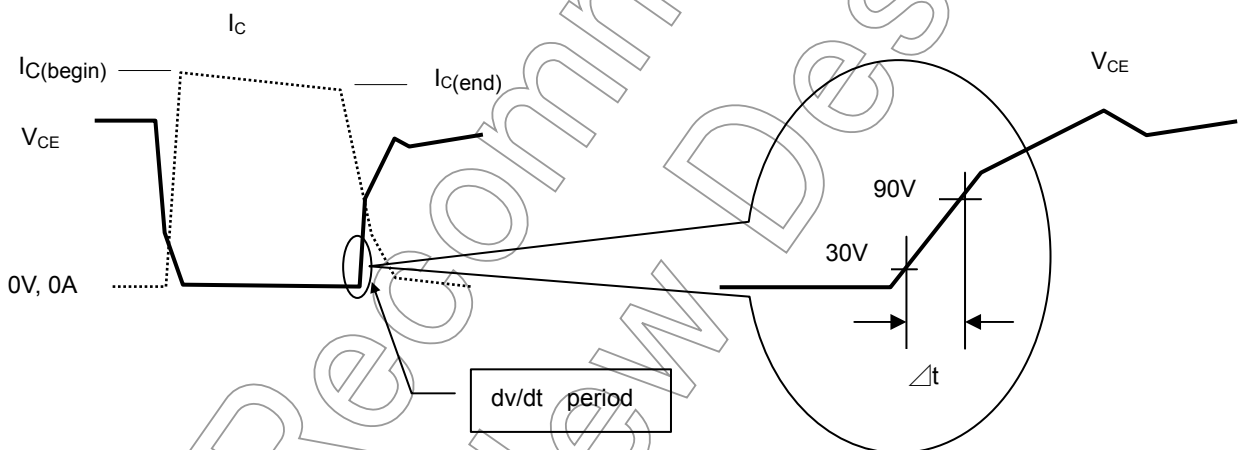
●definition of dv/dt

The slope of V_{CE} from 30v to 90v (attached figure.1)

$$dv/dt = (90V-30V) / (\Delta t)$$

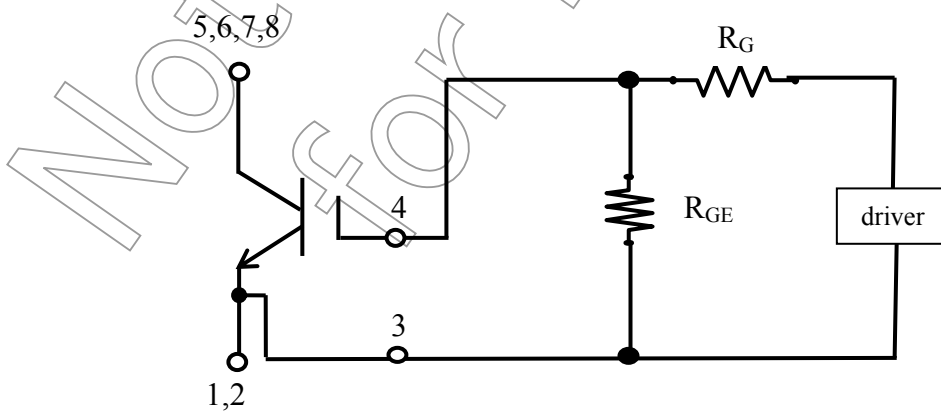
$$= 60V / \Delta t$$

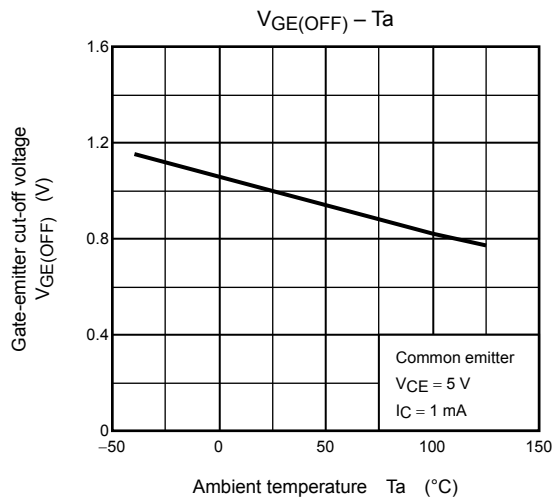
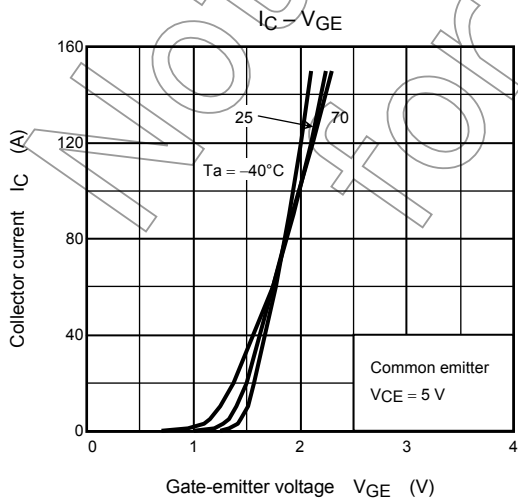
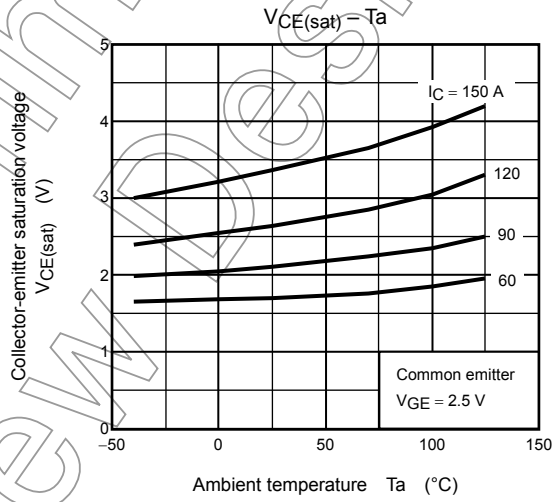
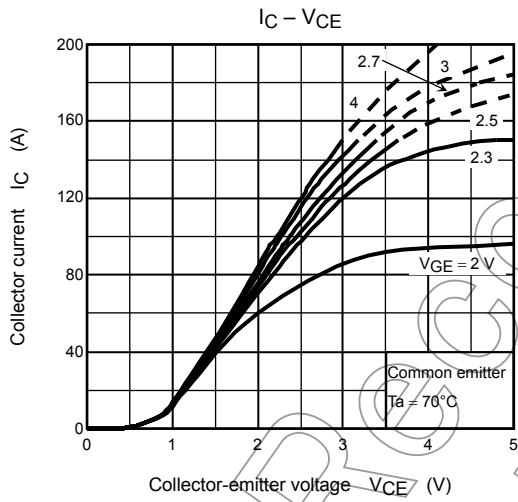
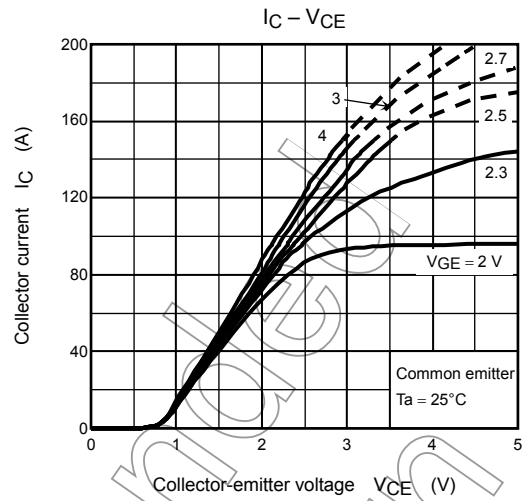
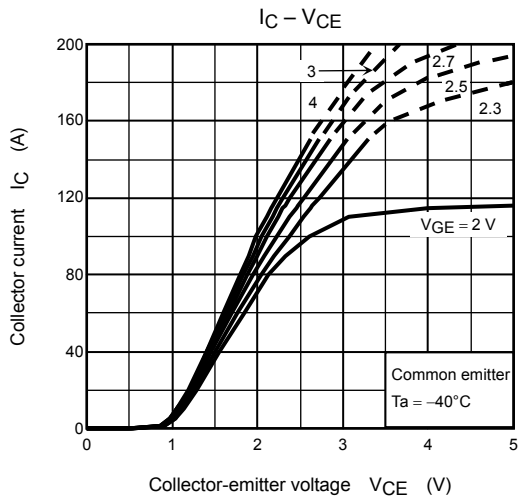
●waveform

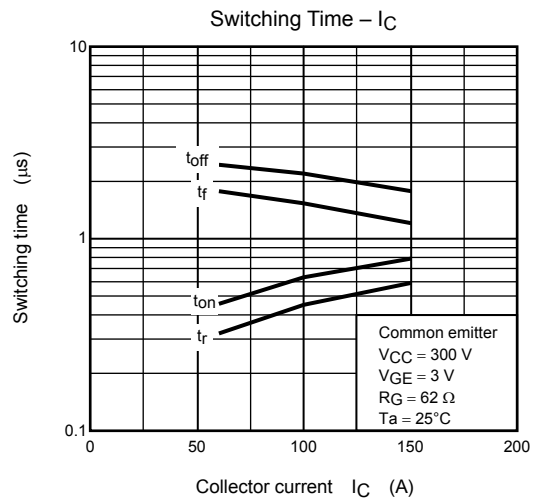
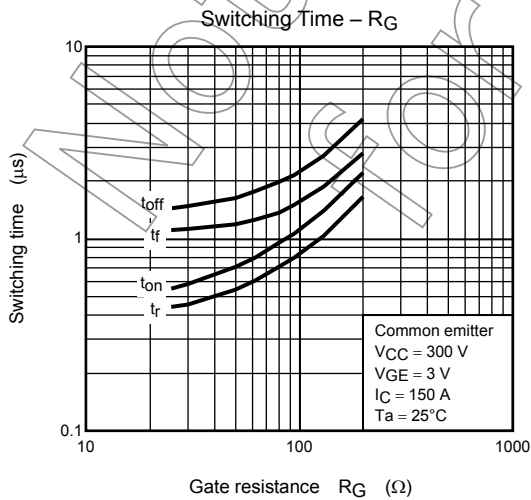
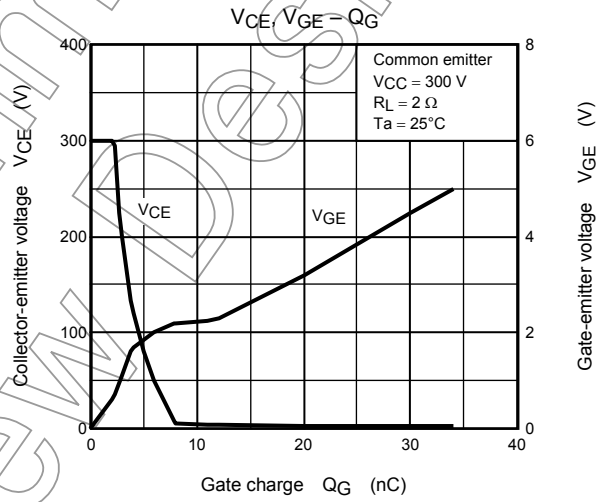
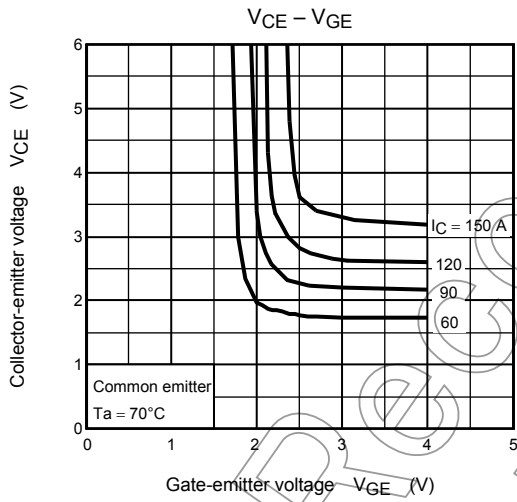
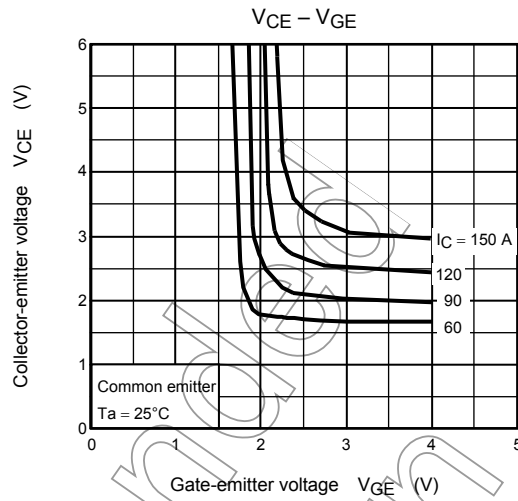
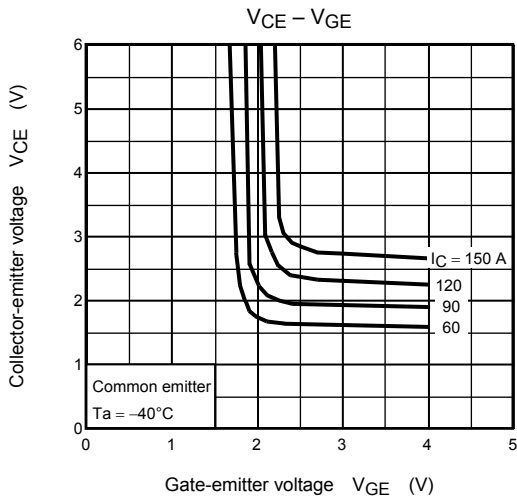


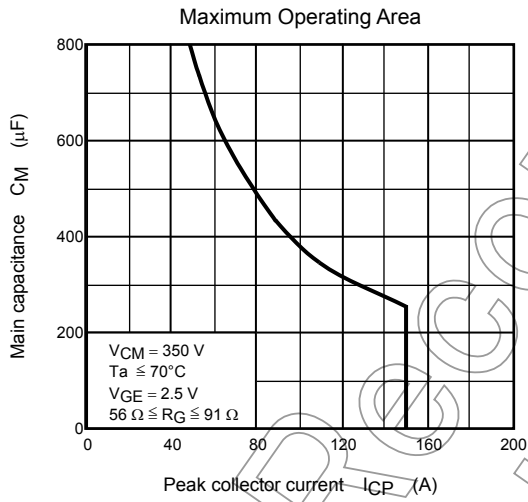
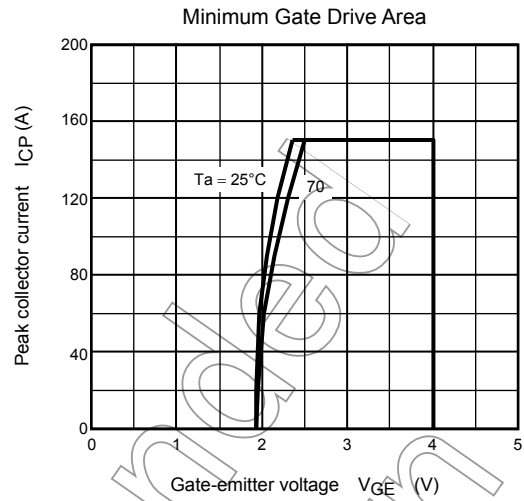
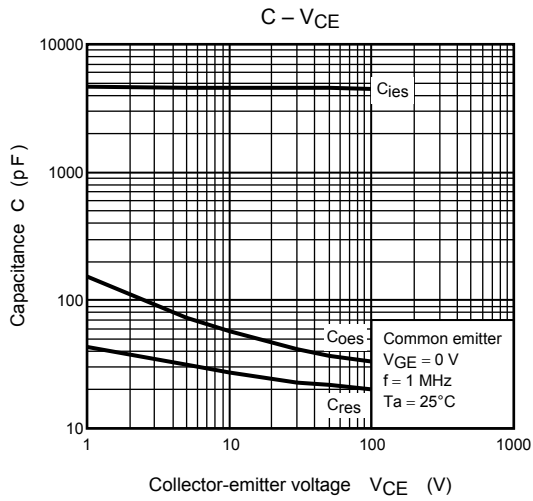
●waveform (expansion)

●Gate drive connection









Not for New Design

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20070701-EN

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